

ABSTRACT OF THE DISCLOSURE

PH BUFFERED AQUEOUS CLEANING COMPOSITION AND METHOD FOR REMOVING PHOTORESIST RESIDUE

A residue cleaning composition includes: (a) water; (b) a fluoride; (c) a pH buffer system including an organic acid and a base. The organic acid can be an

- 5 aminoalkylsulfonic acid and/or an aminoalkylcarboxylic acid. The base can be an amine and/or a quaternary alkylammonium hydroxide. The composition is substantially free of an added organic solvent and has a pH ranging from about 5 to about 12. A method of removing residue from a substrate includes contacting the residue with the cleaning composition. A method for defining a pattern includes etching the pattern through a
- 10 photoresist into a substrate, heating the patterned substrate to a temperature sufficient to ash the photoresist and provide a residue, and removing the residue by contacting the residue with the cleaning composition.